Microchip Technology - A3PE3000-1PQG208I Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	147
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe3000-1pqg208i

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

I/Os Per Package[1]

ProASIC3E Devices	A3PE600		A3PE1500 [3]		A3PE3000 [3]	
Cortex-M1 Devices [2]			M1A3PE1500		M1A3PE3000	
	I/O Types					
Package	Single-Ended I/O[1]	Differential I/O Pairs	Single-Ended I/O[1]	Differential I/O Pairs	Single-Ended I/O[1]	Differential I/O Pairs
PQ208	147	65	147	65	147	65
FG256	165	79	–	–	–	–
FG324	–	–	–	–	221	110
FG484	270	135	280	139	341	168
FG676	–	–	444	222	–	–
FG896	–	–	–	–	620	310

Notes:

1. *When considering migrating your design to a lower- or higher-density device, refer to the ProASIC3E FPGA Fabric User's Guide to ensure compliance with design and board migration requirements.*
2. *Each used differential I/O pair reduces the number of single-ended I/Os available by two.*
3. *For A3PE1500 and A3PE3000 devices, the usage of certain I/O standards is limited as follows:*
   - *– SSTL3(I) and (II): up to 40 I/Os per north or south bank*
   - *– LVPECL / GTL+ 3.3 V / GTL 3.3 V: up to 48 I/Os per north or south bank*
   - *– SSTL2(I) and (II) / GTL+ 2.5 V/ GTL 2.5 V: up to 72 I/Os per north or south bank*
4. *FG256 and FG484 are footprint-compatible packages.*
5. *When using voltage-referenced I/O standards, one I/O pin should be assigned as a voltage-referenced pin (VREF) per minibank (group of I/Os).*
6. *"G" indicates RoHS-compliant packages. Refer to the "ProASIC3E Ordering Information" on page III for the location of the "G" in the part number.*

Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions

Package	PQ208	FG256	FG324	FG484	FG676	FG896
Length × Width (mm\mm)	28 × 28	17 × 17	19 × 19	23 × 23	27 × 27	31 × 31
Nominal Area (mm^2)	784	289	361	529	729	961
Pitch (mm)	0.5	1.0	1.0	1.0	1.0	1.0
Height (mm)	3.40	1.60	1.63	2.23	2.23	2.23

ProASIC3E Device Status

ProASIC3E Devices	Status	M1 ProASIC3E Devices	Status
A3PE600	Production		
A3PE1500	Production	M1A3PE1500	Production
A3PE3000	Production	M1A3PE3000	Production

ProASIC3E Ordering Information

A3PE3000 – 1 FG G 896 I Y

Security Feature
Y = Device Includes License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio
Note: *Only devices with packages greater than or equal to 5x5 are supported*
Blank = Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio

Application (Temperature Range)
Blank = Commercial (0°C to +85°C Junction Temperature)
I = Industrial (–40°C to +100°C Junction Temperature)
PP = Pre-Production
ES = Engineering Sample (Room Temperature Only)

Package Lead Count

Lead-Free Packaging
Blank = Standard Packaging
G = RoHS-Compliant (Green) Packaging

Package Type
PQ = Plastic Quad Flat Pack (0.5 mm pitch)
FG = Fine Pitch Ball Grid Array (1.0 mm pitch)

Speed Grade
1 = 15% Faster than Standard
2 = 25% Faster than Standard

Part Number

ProASIC3E Devices

A3PE600 = 600,000 System Gates
A3PE1500 = 1,500,000 System Gates
A3PE3000 = 3,000,000 System Gates

ProASIC3E Devices with Cortex-M1

M1A3PE1500 = 1,500,000 System Gates
M1A3PE3000 = 3,000,000 System Gates

Table 2-2 • **Recommended Operating Conditions** [1]

Symbol	Parameter		Commercial	Industrial	Units
T_A	Ambient temperature		0 to +70	–40 to +85	°C
T_J	Junction temperature		0 to +85	–40 to +100	°C
VCC	1.5 V DC core supply voltage		1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode[2]	3.15 to 3.45	3.15 to 3.45	V
		Operation[3]	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)		1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV [4]	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	3.0 V DC supply voltage[5]		2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. *All parameters representing voltages are measured with respect to GND unless otherwise specified.*
2. *The programming temperature range supported is $T_{ambient}$ = 0°C to 85°C.*
3. *VPUMP can be left floating during normal operation (not programming mode).*
4. *The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-13 on page 2-16. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.*
5. *To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.*
6. *3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.*

Table 2-3 • **Flash Programming Limits – Retention, Storage and Operating Temperature** [1]

Product Grade	Programming Cycles	Program Retention (biased/unbiased)	Maximum Storage Temperature T_{STG} (°C) [2]	Maximum Operating Junction Temperature T_J (°C) [2]
Commercial	500	20 years	110	100
Industrial	500	20 years	110	100

Notes:

1. *This is a stress rating only; functional operation at any condition other than those indicated is not implied.*
2. *These limits apply for program/data retention only. Refer to Table 2-1 on page 2-1 and Table 2-2 for device operating conditions and absolute limits.*

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-11 on page 2-11.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-12 on page 2-11.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-12 on page 2-11. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-11 on page 2-11.

F_{CLK} is the global clock signal frequency.

Timing Characteristics

***Table 2-31* • 3.3 V LVCMOS Wide Range High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	4 mA	Std.	0.66	12.19	0.04	1.83	2.38	0.43	12.19	10.17	4.16	4.00	15.58	13.57	ns
		–1	0.56	10.37	0.04	1.55	2.02	0.36	10.37	8.66	3.54	3.41	13.26	11.54	ns
		–2	0.49	9.10	0.03	1.36	1.78	0.32	9.10	7.60	3.11	2.99	11.64	10.13	ns
100 µA	8 mA	Std.	0.66	7.85	0.04	1.83	2.38	0.43	7.85	6.29	4.71	4.97	11.24	9.68	ns
		–1	0.56	6.68	0.04	1.55	2.02	0.36	6.68	5.35	4.01	4.22	9.57	8.24	ns
		–2	0.49	5.86	0.03	1.36	1.78	0.32	5.86	4.70	3.52	3.71	8.40	7.23	ns
100 µA	12 mA	Std.	0.66	5.67	0.04	1.83	2.38	0.43	5.67	4.36	5.06	5.59	9.07	7.75	ns
		–1	0.56	4.82	0.04	1.55	2.02	0.36	4.82	3.71	4.31	4.75	7.71	6.59	ns
		–2	0.49	4.24	0.03	1.36	1.78	0.32	4.24	3.25	3.78	4.17	6.77	5.79	ns
100 µA	16 mA	Std.	0.66	5.35	0.04	1.83	2.38	0.43	5.35	3.96	5.15	5.76	8.75	7.35	ns
		–1	0.56	4.55	0.04	1.55	2.02	0.36	4.55	3.36	4.38	4.90	7.44	6.25	ns
		–2	0.49	4.00	0.03	1.36	1.78	0.32	4.00	2.95	3.85	4.30	6.53	5.49	ns
100 µA	24 mA	Std.	0.66	4.96	0.04	1.83	2.38	0.43	4.96	3.27	5.23	6.38	8.35	6.67	ns
		–1	0.56	4.22	0.04	1.55	2.02	0.36	4.22	2.78	4.45	5.43	7.11	5.67	ns
		–2	0.49	3.70	0.03	1.36	1.78	0.32	3.70	2.44	3.91	4.76	6.24	4.98	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Software default selection highlighted in gray.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Timing Characteristics

Table 2-35 • 2.5 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.82	0.04	1.51	1.66	0.43	8.13	8.82	2.72	2.29	10.37	11.05	ns
	–1	0.56	7.50	0.04	1.29	1.41	0.36	6.92	7.50	2.31	1.95	8.82	9.40	ns
	–2	0.49	6.58	0.03	1.13	1.24	0.32	6.07	6.58	2.03	1.71	7.74	8.25	ns
8 mA	Std.	0.66	5.27	0.04	1.51	1.66	0.43	5.27	5.27	3.10	3.03	7.50	7.51	ns
	–1	0.56	4.48	0.04	1.29	1.41	0.36	4.48	4.48	2.64	2.58	6.38	6.38	ns
	–2	0.49	3.94	0.03	1.13	1.24	0.32	3.93	3.94	2.32	2.26	5.60	5.61	ns
12 mA	Std.	0.66	3.74	0.04	1.51	1.66	0.43	3.81	3.49	3.37	3.49	6.05	5.73	ns
	–1	0.56	3.18	0.04	1.29	1.41	0.36	3.24	2.97	2.86	2.97	5.15	4.87	ns
	–2	0.49	2.80	0.03	1.13	1.24	0.32	2.85	2.61	2.51	2.61	4.52	4.28	ns
16 mA	Std.	0.66	3.53	0.04	1.51	1.66	0.43	3.59	3.12	3.42	3.62	5.83	5.35	ns
	–1	0.56	3.00	0.04	1.29	1.41	0.36	3.06	2.65	2.91	3.08	4.96	4.55	ns
	–2	0.49	2.63	0.03	1.13	1.24	0.32	2.68	2.33	2.56	2.71	4.35	4.00	ns
24 mA	Std.	0.66	3.26	0.04	1.51	1.66	0.43	3.32	2.48	3.49	4.11	5.56	4.72	ns
	–1	0.56	2.77	0.04	1.29	1.41	0.36	2.83	2.11	2.97	3.49	4.73	4.01	ns
	–2	0.49	2.44	0.03	1.13	1.24	0.32	2.48	1.85	2.61	3.07	4.15	3.52	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

2.5 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

***Table 2-57* • Minimum and Maximum DC Input and Output Levels**

2.5 V GTL+	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	μA[2]	μA[2]
33 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

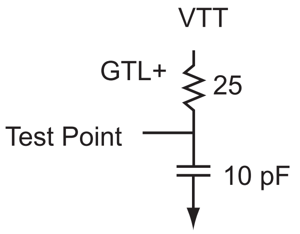

***Figure 2-15* • AC Loading**

***Table 2-58* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

***Table 2-59* • 2.5 V GTL+**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 2.3 V, VREF = 1.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.21	0.04	1.51	0.43	2.25	2.10			4.48	4.34	ns
–1	0.51	1.88	0.04	1.29	0.36	1.91	1.79			3.81	3.69	ns
–2	0.45	1.65	0.03	1.13	0.32	1.68	1.57			3.35	3.24	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

SSTL2 Class II

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-69 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
18 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

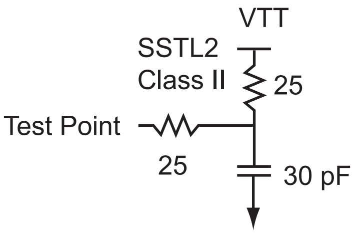

Figure 2-19 • AC Loading

Table 2-70 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-71 • SSTL 2 Class II
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	0.66	2.17	0.04	1.33	0.43	2.21	1.77			4.44	ns
–1	0.56	0.56	1.84	0.04	1.14	0.36	1.88	1.51			3.78	ns
–2	0.49	0.49	1.62	0.03	1.00	0.32	1.65	1.32			3.32	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-24. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

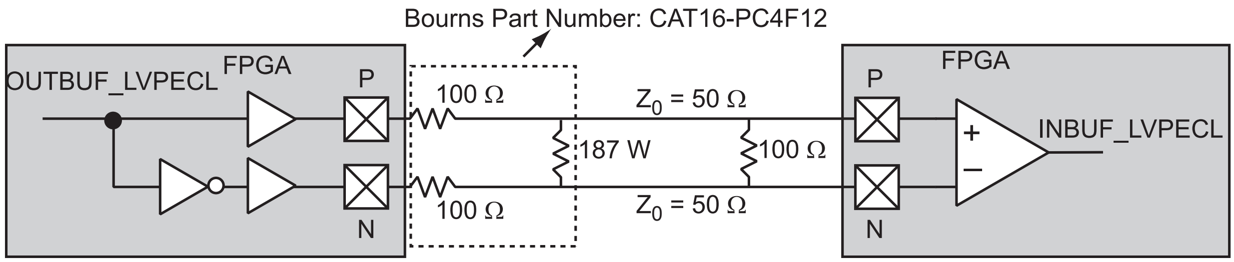

Figure 2-24 **• LVPECL Circuit Diagram and Board-Level Implementation**

Table 2-81 **• Minimum and Maximum DC Input and Output Levels**

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-82 **• AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)
1.64	1.94	Cross point	–

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-83 **• LVPECL**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.66	1.83	0.04	1.63	ns
–1	0.56	1.55	0.04	1.39	ns
–2	0.49	1.36	0.03	1.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Table 2-84 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-25 on page 2-53 for more information.

***Table 2-85* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

Note: *See Figure 2-26 on page 2-55 for more information.

Output Register

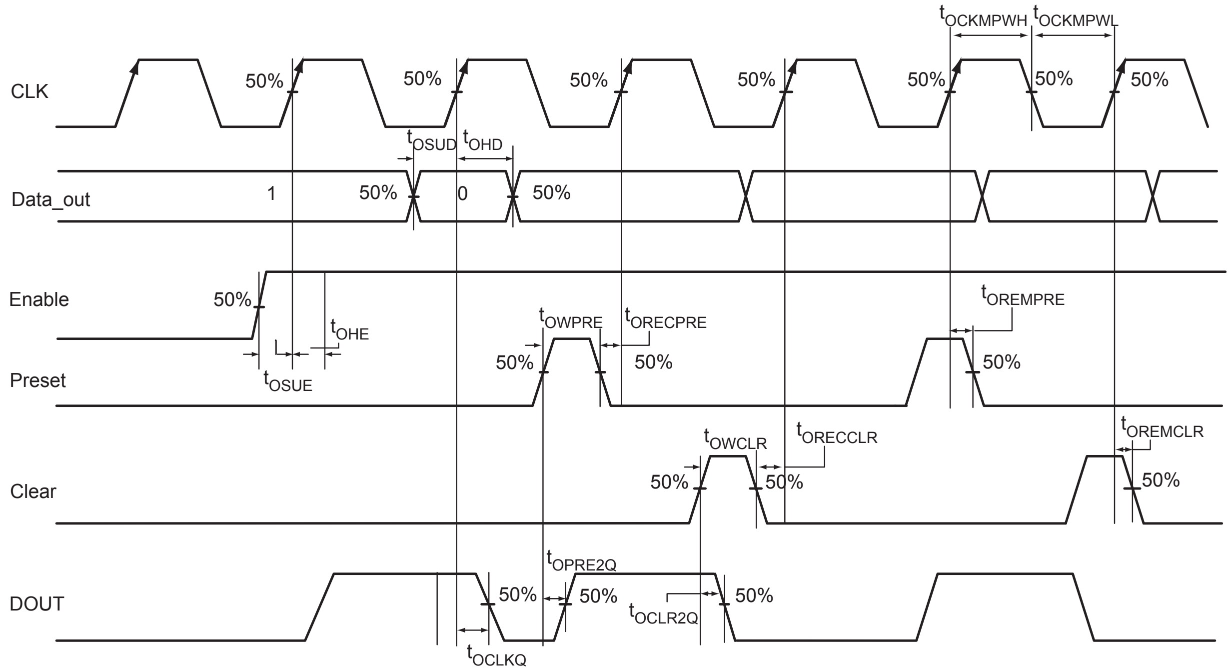

***Figure 2-28* • Output Register Timing Diagram**

Timing Characteristics

***Table 2-87* • Output Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.59	0.67	0.79	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.31	0.36	0.42	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.44	0.50	0.59	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.80	0.91	1.07	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.80	0.91	1.07	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.22	0.25	0.30	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.22	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.36	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Output Enable Register

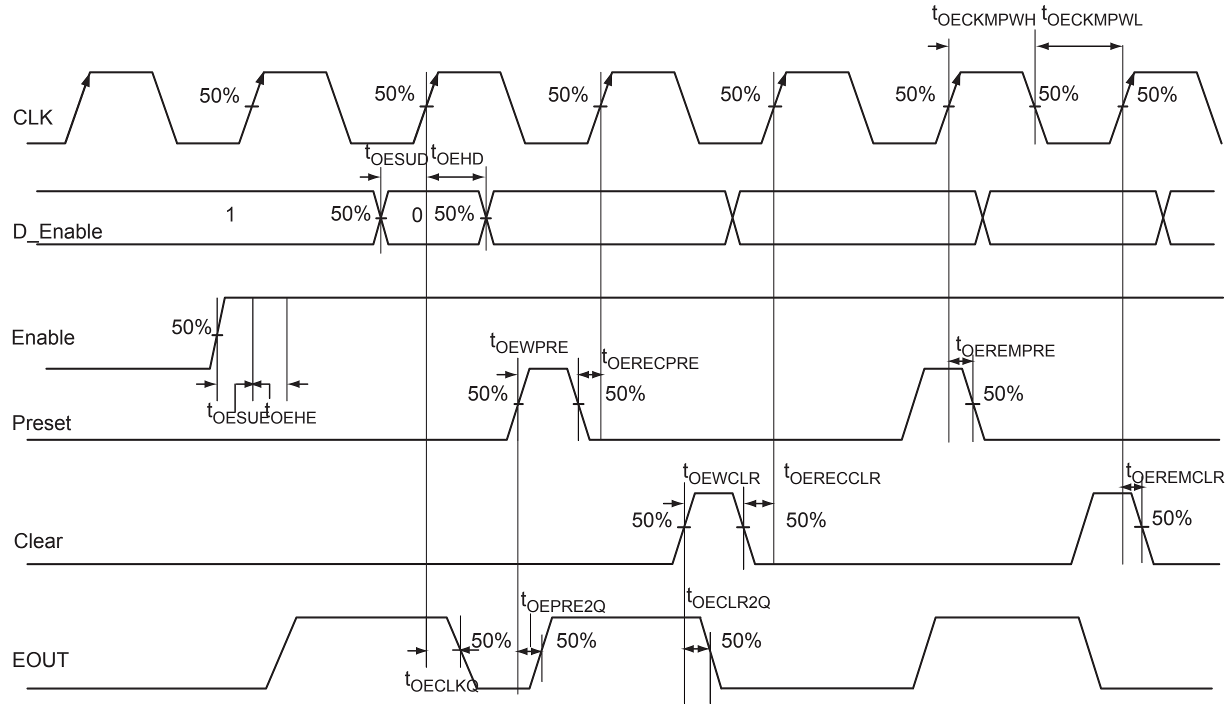

Figure 2-29 **• Output Enable Register Timing Diagram**

Timing Characteristics

Table 2-88 **• Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.59	0.67	0.79	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.31	0.36	0.42	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.44	0.50	0.58	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.67	0.76	0.89	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.22	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.36	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.32	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

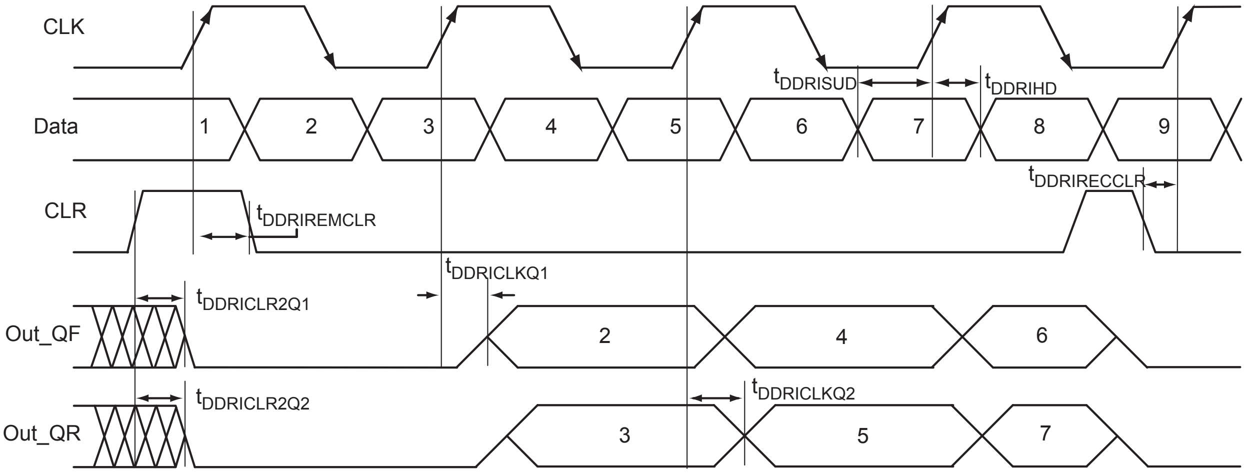

Figure 2-31 • **Input DDR Timing Diagram**

Timing Characteristics

Table 2-90 • **Input DDR Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.39	0.44	0.52	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.27	0.31	0.37	ns
$t_{DDRISUD}$	Data Setup for Input DDR	0.28	0.32	0.38	ns
t_{DDRIHD}	Data Hold for Input DDR	0.00	0.00	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear to Out Out_QR for Input DDR	0.57	0.65	0.76	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.46	0.53	0.62	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	0.00	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.22	0.25	0.30	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	1404	1232	1048	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

FG256	
Pin Number	**A3PE600 Function**
P9	IO82PDB5V0
P10	IO76NDB4V1
P11	IO76PDB4V1
P12	VMV4
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO67NDB3V1
R1	GEA1/IO102PDB6V0
R2	GEA0/IO102NDB6V0
R3	GNDQ
R4	GEC2/IO99PDB5V2
R5	IO95NPB5V1
R6	IO91NDB5V1
R7	IO91PDB5V1
R8	IO83NDB5V0
R9	IO83PDB5V0
R10	IO77NDB4V1
R11	IO77PDB4V1
R12	IO69NDB4V0
R13	GDB2/IO69PDB4V0
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO100NDB5V2
T3	GEB2/IO100PDB5V2
T4	IO99NDB5V2
T5	IO88NDB5V0
T6	IO88PDB5V0
T7	IO89NSB5V0
T8	IO80NSB4V1
T9	IO81NDB4V1
T10	IO81PDB4V1
T11	IO70NDB4V0
T12	GDC2/IO70PDB4V0

FG256	
Pin Number	**A3PE600 Function**
T13	IO68NDB4V0
T14	GDA2/IO68PDB4V0
T15	TMS
T16	GND

FG676	
Pin Number	**A3PE1500 Function**
A1	GND
A2	GND
A3	GAA0/IO00NDB0V0
A4	GAA1/IO00PDB0V0
A5	IO06NDB0V0
A6	IO09NDB0V1
A7	IO09PDB0V1
A8	IO14NDB0V1
A9	IO14PDB0V1
A10	IO22NDB0V2
A11	IO22PDB0V2
A12	IO26NDB0V3
A13	IO26PDB0V3
A14	IO30NDB0V3
A15	IO30PDB0V3
A16	IO34NDB1V0
A17	IO34PDB1V0
A18	IO38NDB1V0
A19	IO38PDB1V0
A20	IO41PDB1V1
A21	IO44PDB1V1
A22	IO49PDB1V2
A23	IO50PDB1V2
A24	GBC1/IO55PDB1V3
A25	GND
A26	GND
AA1	IO174PDB6V0
AA2	IO171PDB6V0
AA3	GEA1/IO167PPB6V0
AA4	GEC0/IO169NPB6V0
AA5	VCOMPLE
AA6	GND
AA7	IO165NDB5V3
AA8	GEB2/IO165PDB5V3
AA9	IO163PDB5V3
AA10	IO159NDB5V3
AA11	IO153NDB5V2
AA12	IO147NDB5V1
AA13	IO139NDB5V0
AA14	IO137NDB5V0
AA15	IO123NDB4V1
AA16	IO123PDB4V1
AA17	IO117NDB4V0
AA18	IO117PDB4V0
AA19	GDB2/IO112PDB4V0
AA20	GNDQ
AA21	TDO
AA22	GND
AA23	GND
AA24	IO102NDB3V1
AA25	IO102PDB3V1
AA26	IO98NDB3V1
AB1	IO174NDB6V0
AB2	IO171NDB6V0
AB3	GEB1/IO168PPB6V0
AB4	GEA0/IO167NPB6V0
AB5	VCCPLE
AB6	GND
AB7	GND
AB8	IO156NDB5V2
AB9	IO156PDB5V2
AB10	IO150PDB5V1
AB11	IO155PDB5V2
AB12	IO142PDB5V0
AB13	IO135NDB5V0
AB14	IO135PDB5V0
AB15	IO132PDB4V2
AB16	IO129PDB4V2
AB17	IO121PDB4V1
AB18	IO119NDB4V1
AB19	IO112NDB4V0
AB20	VMV4
AB21	TCK
AB22	TRST
AB23	GDC0/IO108NDB3V2
AB24	GDC1/IO108PDB3V2
AB25	IO104NDB3V2
AB26	IO104PDB3V2
AC1	IO170PDB6V0
AC2	GEB0/IO168NPB6V0
AC3	IO166NPB5V3
AC4	GNDQ
AC5	GND
AC6	IO160PDB5V3
AC7	IO161PDB5V3
AC8	IO154PDB5V2
AC9	GND
AC10	IO150NDB5V1
AC11	IO155NDB5V2
AC12	IO142NDB5V0
AC13	IO138NDB5V0
AC14	IO138PDB5V0
AC15	IO132NDB4V2
AC16	IO129NDB4V2
AC17	IO121NDB4V1
AC18	IO119PDB4V1
AC19	IO118NDB4V0
AC20	IO118PDB4V0
AC21	IO114PPB4V0
AC22	TMS
AC23	VJTAG
AC24	VMV3
AC25	IO106NDB3V2
AC26	IO106PDB3V2
AD1	IO170NDB6V0
AD2	GEA2/IO166PPB5V3
AD3	VMV5
AD4	GEC2/IO164PDB5V3

FG676	
Pin Number	**A3PE1500 Function**
L17	GND
L18	VCC
L19	VCCIB2
L20	IO67PDB2V1
L21	IO67NDB2V1
L22	IO71PDB2V2
L23	IO71NDB2V2
L24	GNDQ
L25	IO82PDB2V3
L26	IO84NDB2V3
M1	IO198NPB7V0
M2	IO202PDB7V1
M3	IO202NDB7V1
M4	IO206NDB7V1
M5	IO206PDB7V1
M6	IO204NDB7V1
M7	IO204PDB7V1
M8	VCCIB7
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	GND
M15	GND
M16	GND
M17	GND
M18	VCC
M19	VCCIB2
M20	IO73NDB2V2
M21	IO73PDB2V2
M22	IO81PPB2V3
M23	IO77PDB2V2
M24	IO77NDB2V2
M25	IO82NDB2V3
M26	IO83PDB2V3

FG676	
Pin Number	**A3PE1500 Function**
N1	GFB0/IO191NPB7V0
N2	VCOMPLF
N3	GFB1/IO191PPB7V0
N4	IO196PDB7V0
N5	GFA0/IO190NDB6V2
N6	IO200PDB7V1
N7	IO200NDB7V1
N8	VCCIB7
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	GND
N15	GND
N16	GND
N17	GND
N18	VCC
N19	VCCIB2
N20	IO79PDB2V3
N21	IO79NDB2V3
N22	GCA2/IO88PPB3V0
N23	IO81NPB2V3
N24	GCA0/IO87NDB3V0
N25	GCB0/IO86NPB2V3
N26	IO83NDB2V3
P1	GFA2/IO189PDB6V2
P2	VCCPLF
P3	IO193PPB7V0
P4	IO196NDB7V0
P5	GFA1/IO190PDB6V2
P6	IO194PDB7V0
P7	IO194NDB7V0
P8	VCCIB6
P9	VCC
P10	GND

FG676	
Pin Number	**A3PE1500 Function**
P11	GND
P12	GND
P13	GND
P14	GND
P15	GND
P16	GND
P17	GND
P18	VCC
P19	VCCIB3
P20	GCC0/IO85NDB2V3
P21	GCC1/IO85PDB2V3
P22	GCB1/IO86PPB2V3
P23	IO88NPB3V0
P24	GCA1/IO87PDB3V0
P25	VCCPLC
P26	VCOMPLC
R1	IO189NDB6V2
R2	IO185PDB6V2
R3	IO187NPB6V2
R4	IO193NPB7V0
R5	GFC2/IO187PPB6V2
R6	GFC1/IO192PDB7V0
R7	GFC0/IO192NDB7V0
R8	VCCIB6
R9	VCC
R10	GND
R11	GND
R12	GND
R13	GND
R14	GND
R15	GND
R16	GND
R17	GND
R18	VCC
R19	VCCIB3
R20	NC

Revision	Changes	Page
Revision 10 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34669).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "ProASIC3E Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34727).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34689).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34699).	1-6
	VCCPLL in Table 2-2 • Recommended Operating Conditions [1] was corrected from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 33851). The T_J symbol was added to the table and notes regarding T_A and T_J were removed. The second of two parameters in the VCCI and VMV row, called "3.3 V DC supply voltage," was corrected to "3.0 V DC supply voltage" (SAR 37227).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide* (SAR 34735).	2-9
	t_{DOUT} was corrected to t_{DIN} in Figure 2-3 • Input Buffer Timing Model and Delays (example) (SAR 37109).	2-13
	The typo related to the values for 3.3 V LVCMOS Wide Range in Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings was corrected (SAR 37227).	2-19
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section and "3.3 V LVCMOS Wide Range" section and tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34763).	2-18, 2-27

Revision	Changes	Page
Advance v0.5 (continued)	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Introduction" section was updated.	2-28
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-35 • ProASIC3E I/O Features was updated.	2-54
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-37 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in ProASIC3E Devices (maximum drive strength and high slew selected).	2-55
	Table 2-48 • ProASIC3E I/O Attributes vs. I/O Standard Applications	2-81
	Table 2-55 • ProASIC3 I/O Standards—SLEW and Output Drive (OUT_DRIVE) Settings	2-85
	The "x" was updated in the "Pin Descriptions" section.	2-50
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	EXTFB was removed from Figure 2-24 • ProASIC3E CCC Options.	2-24
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-13 • ProASIC3E CCC/PLL Specification.	2-30
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	The LVPECL specification in Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Table 2-15 • Levels of Hot-Swap Support was updated.	2-34
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50

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